2SC5026

Silicon NPN epitaxial planar type

For low-frequency output amplification Complementary to 2SA1890

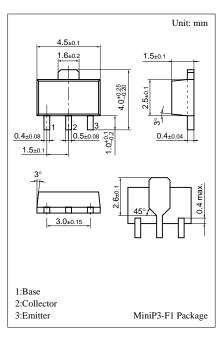
Features

- Low collector to emitter saturation voltage V_{CE(sat)}.
- High collector to emitter voltage V_{CEO}.
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	80	V
Collector to emitter voltage	V_{CEO}	80	V
Emitter to base voltage	V_{EBO}	5	V
Peak collector current	I_{CP}	1.5	A
Collector current	I_{C}	1	A
Collector power dissipation	${P_C}^*$	1	W
Junction temperature	T _j	150	°C
Storage temperature	$T_{\rm stg}$	−55 ~ +150	°C

^{*} Printed circuit board: Copper foil area of 1cm² or more, and the board thickness of 1.7mm for the collector portion



Marking symbol: 2A

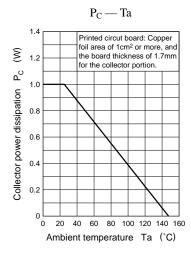
Electrical Characteristics (Ta=25°C)

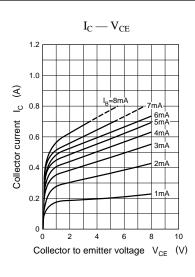
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 40V, I_{E} = 0$			0.1	μА
Collector to base voltage	V _{CBO}	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$	80			V
Collector to emitter voltage	V _{CEO}	$I_C = 1 \text{mA}, I_B = 0$	80			V
Emitter to base voltage	V _{EBO}	$I_{\rm E} = 10 \mu A, I_{\rm C} = 0$	5			V
	h _{FE1} *1	$V_{CE} = 2V, I_{C} = 100mA$	120		340	
Forward current transfer ratio	h _{FE2}	$V_{CE} = 2V, I_{C} = 500 \text{mA}^{*2}$	60			
Collector to emitter saturation voltage	V _{CE(sat)}	$I_C = 500 \text{mA}, I_B = 50 \text{mA}^{*2}$		0.15	0.3	V
Base to emitter saturation voltage	V _{BE(sat)}	$I_C = 500 \text{mA}, I_B = 50 \text{mA}^{*2}$		0.85	1.2	V
Transition frequency	f_T	$V_{CB} = 10V, I_{E} = -50mA, f = 200MHz$		120		MHz
Collector output capacitance	C _{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		10	20	pF

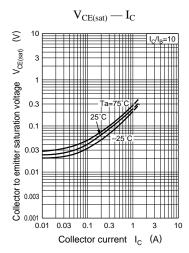
^{*2} Pulse measurement

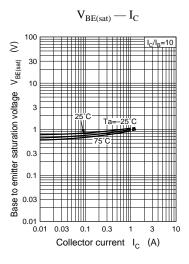
^{*1}hFE Rank classification

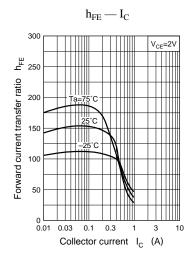
Rank	R	S
h_{FE1}	120 ~ 240	170 ~ 340

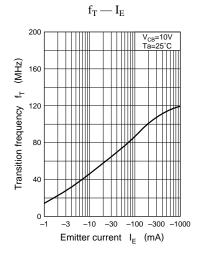


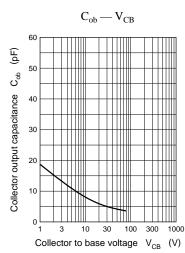












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